

### **AMENDMENTS TO THE SPECIFICATION**

Please amend paragraph [0036] of the specification as follows:

Then, as shown in Fig. 3C and Fig. 6, a color filter 112 including color filter layers R(red), G(green) and B(blue) is formed in a stripe shape. In order to form the color filter 112 including the color filter layers of R, G and B, a process of depositing a color resin and patterning it is repeated three times. At this point, the color filter 112 for each TFT overlaps ~~an~~ a side portion of the data line 101b and an end portion of the drain electrode 108, denoted as the regions "T" in Fig. 3C, so as to prevent light leakage and to improve an aperture ratio. Because boundary of adjacent color filter stripes is located on the center portion of the data line, it can provide a sharp, immutable boundary between color filter stripe. Bleeding of adjoining color filters to each other and blurring of boundaries can be also avoided. The color filter can overlap a portion of source electrode 106. Thereafter, using the source and drain electrodes 106 and 108 as a mask, a portion of the doped amorphous silicon layer 104b between the source and drain electrodes 106 and 108 is etched by a dry or a wet-etching technique to form a channel region.